

MA721

Silicon epitaxial planer type

For super high speed switching circuit
For small current rectification

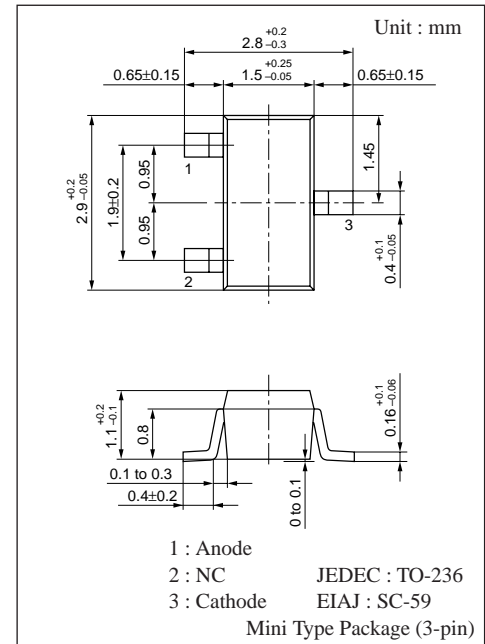
■ Features

- Seal in the mini mold package, Automatic insertion possible
- $I_{F(AV)} = 200\text{mA}$ rectification possible
- Superior in reliability

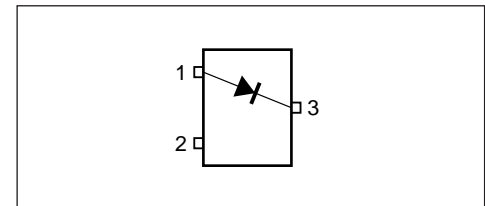
■ Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Rating	Unit
Reverse voltage (DC)	V_R	30	V
Non-repetitive peak forward current	I_{FSM}^*	1	A
Peak forward current	I_{FM}	300	mA
Average forward current	$I_{F(AV)}$	200	mA
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	- 55 to + 150	$^\circ\text{C}$

* 50Hz sine wave, one-cycle wave, high value (non-repetitive)



■ Internal Connection



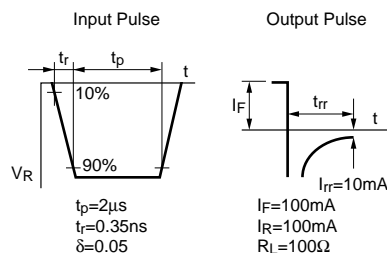
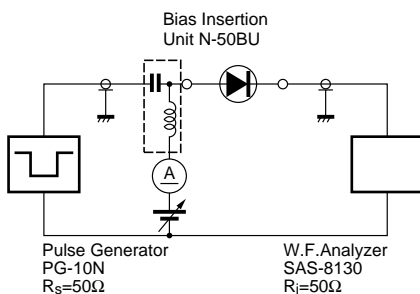
■ Electrical Characteristics ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Condition	min	typ	max	Unit
Reverse current (DC)	I_R	$V_R = 30\text{V}$			50	μA
Forward voltage (DC)	V_F	$I_F = 200\text{mA}$			0.55	V
Terminal capacitance	C_t	$V_R = 0\text{V}, f = 1\text{MHz}$		30		pF
Reverse recovery time	t_{rr}^*	$I_F = I_R = 100\text{mA}$ $I_{rr} = 10\text{mA}, R_L = 100\Omega$		3.0		ns

Note 1. Schottky barrier diode is sensitive to electric shock (static electricity, etc.). Due attention must be paid on charge of a human body and leakage from the equipment used.

2. Rated input/output frequency : 1000MHz

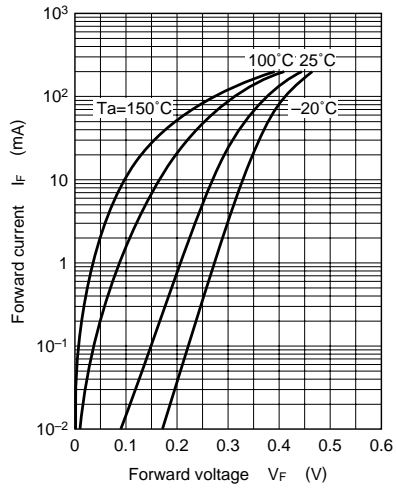
3. * t_{rr} measuring circuit



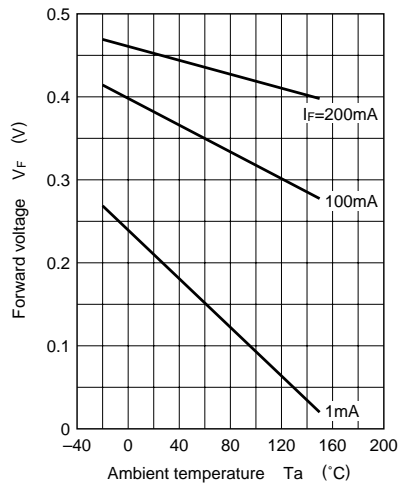
■ Marking



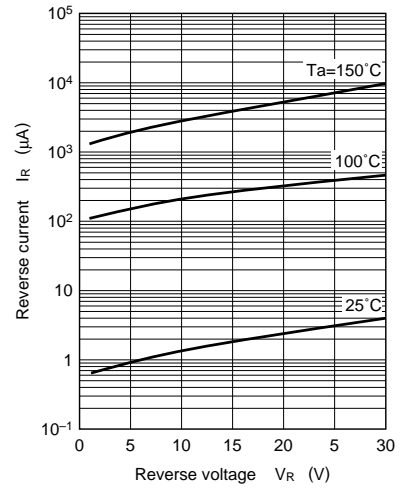
$I_F - V_F$



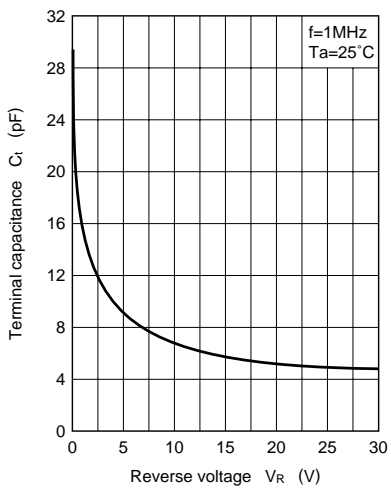
$V_F - T_a$



$I_R - V_R$



$C_t - V_R$



$I_R - T_a$

